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## Depleted CMOS pixels for LHC pp-Experiments

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While so far monolithic pixel detectors have remained in the realm of comparatively low radiation application outside LHC, new developments exploiting high resistivity substrates with three or four well CMOS process options allow fairly large depletion depths and full CMOS circuitry in a monolithic structure. This opens up the possibility to target CMOS pixel detectors also for high radiation pp-experiments at the LHC upgrade, either in a hybrid-type fashion or even fully monolithic. We have prototyped several pixel matrices with high ohmic substrates and full CMOS electronics and characterized them in the lab and in test beams. On the basis of this an ATLAS CMOS demonstrator program has been started. The results available at the time of the meeting will be presented.

**Primary author:** Prof. WERMES, Norbert (University of Bonn)

**Co-authors:** Dr MARINAS, Carlos (University of Bonn); Dr HUEGGING, Fabian (University of Bonn); Dr KRUEGER, Hans (University of Bonn); Dr PERNEGGER, Heinz (CERN Physics Department); Mrs GONELLA, Laura (University of Bonn); Dr BACKHAUS, Malte (CERN); Dr HAVRANEK, Miroslav (Institute of Physics, Prague); Mr RYMASZEWSKI, Piotr (University of Bonn); Mrs FERNANDEZ-PEREZ, Sonia (CERN); Dr KISHISHITA, Tetsuishi (University of Bonn); Mrs OBERMANN, Theresa (University of Bonn); Mr HEMPEREK, Tomasz (University of Bonn)

**Presenter:** Prof. WERMES, Norbert (University of Bonn)

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